

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	196	438/248.ccls.	US-PGPUB; USPAT	OR	OFF	2006/03/02 09:31
L3	344	((trench groov\$6) with (polysilicon "poly-si" polycrystalline silicon si)) same (isolation sti) same nitride same (planari\$8 near2 (coating layer film sog glass material))	US-PGPUB; USPAT	OR	ON	2006/03/02 09:42
L4	32	L3 same (storage node capacitor deep)	US-PGPUB; USPAT	OR	ON	2006/03/02 09:42
L5	196	438/248.ccls.	US-PGPUB; USPAT	OR	OFF	2006/03/02 09:48
L6	4377	((trench groov\$6) with (polysilicon "poly-si" polycrystalline silicon si)) and (isolation sti) and nitride and (planari\$8 near2 (coating layer film sog glass material))	US-PGPUB; USPAT	OR	ON	2006/03/02 09:48
L7	35	L5 and L6	US-PGPUB; USPAT	OR	ON	2006/03/02 09:48
L9	143	((trench groov\$6) with (polysilicon "poly-si" polycrystalline silicon si)) and (isolation sti) and nitride and (planari\$8 near2 (coating layer film sog glass material))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/02 09:52
L10	12	L9 and (storage node capacitor deep)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/02 09:52
L11	143	((trench groov\$6) with (polysilicon "poly-si" polycrystalline silicon si)) and (isolation sti) and nitride and (planari\$8 near2 (coating layer film sog glass material))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/02 09:54
L12	3	L5 and L3	US-PGPUB; USPAT	OR	ON	2006/03/02 09:57
L13	241	((trench groov\$6) with (polysilicon "poly-si" polycrystalline silicon si)) with (isolation sti)) same nitride same (planari\$8 near2 (coating layer film sog glass material))	US-PGPUB; USPAT	OR	ON	2006/03/02 09:58
L14	173	((trench groov\$6) and (polysilicon "poly-si" polycrystalline silicon si) and (isolation sti) and (nitride liner) and (planari\$8 near2 (coating layer film sog glass material))))).clm.	US-PGPUB	OR	ON	2006/03/02 10:13

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L15	152	((semiconductor device transistor) and (trench groove) and (polysilicon "poly-si" polycrystalline silicon si) and (isolation sti) and (nitride liner) and (oxide dioxide insulating dielectric) and (planarization near2 (coating layer film sogg glass material))))).clm.	US-PGPUB	OR	ON	2006/03/02 10:17
L16	60	((semiconductor device transistor) and ((trench groove) with (conductor conductive conducting conductively polysilicon "poly-si" polycrystalline silicon si) with (fill stud plug)) and (isolation sti) and (nitride liner) and (oxide dioxide insulating dielectric) and (planarization near2 (coating layer film sogg glass material))))).clm.	US-PGPUB	OR	ON	2006/03/02 11:51
L17	2468	438/243.ccls. 438/248.ccls. 438/268.ccls. 438/296.ccls. 438/391.ccls.	US-PGPUB; USPAT	OR	OFF	2006/03/02 11:47
L18	393	L17 and L6	US-PGPUB; USPAT	OR	ON	2006/03/02 11:47
L19	1647	((trench groove) same (conductor conductive conducting conductively polysilicon "poly-si" polycrystalline silicon si) same (fill stud plug)) and (isolation sti) and ((nitride liner) same (oxide dioxide insulating dielectric) same (planarization near2 (coating layer film sogg glass material))))	US-PGPUB; USPAT	OR	ON	2006/03/02 11:52
L20	190	17 and 19	US-PGPUB; USPAT	OR	ON	2006/03/02 11:52